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FCH085N80

April 2016

N-Channel SuperFET® II MOSFET

800 V, 46 A, 85 mΩ

Features

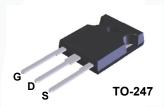
- Typ. $R_{DS(on)}$ = 67 m Ω
- 850 V @ $T_J = 150^{\circ}C$
- Ultra Low Gate Charge (Typ. Q_g = 196 nC)
- Low E_{OSS}(Typ. 18 uJ @ 400 V)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 568 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

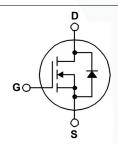
Applications

- · AC-DC Power Supply
- · LED Lighting

Description

SuperFET[®] II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter	FCH085N80_F155	Unit	
V _{DSS}	Drain to Source Voltage		800	V	
	Cata ta Causaa Valtaga	- DC	±20	V	
V_{GSS}	Gate to Source Voltage	- AC (f > 1 Hz)	±30	V	
II_ II)rain (Tirrent L		- Continuous (T _C = 25°C)	46	^	
		- Continuous (T _C = 100°C)	29	A	
I _{DM}	Drain Current	- Pulsed (Note 1)	138	Α	
E _{AS}	Single Pulsed Avalanche Energy	Single Pulsed Avalanche Energy (Note 2)		mJ	
I _{AR}	Avalanche Current	Avalanche Current (Note 1)		Α	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	4.4	mJ	
	MOSFET dv/dt		100	1//	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		20	V/ns	
D	Deves Dissipation	$(T_C = 25^{\circ}C)$	446	W	
P_{D}	Power Dissipation	- Derate Above 25°C	3.5	W/°C	
T _J , T _{STG}	Operating and Storage Temperatu	-55 to +150	°C		
T _L	Maximum Lead Temperature for S	oldering, 1/8" from Case for 5 Seconds	300	°C	

Thermal Characteristics

Symbol	Parameter	FCH085N80_F155	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.28	°C/W
R _{e.IA}	Thermal Resistance, Junction to Ambient, Max.	40.0	30/00

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCH085N80_F155	FCH085N80	TO-247 G03	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}, T_J = 25^{\circ}\text{C}$	800	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 1 mA, Referenced to 25°C	-	0.8	-	V/°C
I	Zero Gate Voltage Drain Current	V _{DS} = 800 V, V _{GS} = 0 V	-	-	25	μΑ
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 640 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	250	μΑ
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 4.6 \text{ mA}$	2.5	-	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 23 A	-	67	85	mΩ
9 _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 23 A	-	55	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 400 V V 0 V	· -	8140	10825	pF
C _{oss}	Output Capacitance	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz	-	255	340	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1/11/12		10	-	pF
C _{oss}	Output Capacitance	V _{DS} = 480 V, V _{GS} = 0 V, f = 1 MHz		1000		pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 480 V, V _{GS} = 0 V	- \	728	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 640 V, I _D = 46 A,	-	196	255	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	40	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	72	-	nC
ESR	Equivalent Series Resistance	f = 1 MHz	-	0.8	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	45	100	ns
t _r		$V_{DD} = 400 \text{ V}, I_D = 46 \text{ A},$	-	55	120	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_g = 4.7 \Omega$	- /	160	330	ns
t _f	Turn-Off Fall Time	(Note 4)	-	35	80	ns

Drain-Source Diode Characteristics

Is	Maximum Continuous Drain to Source Diode Forward Current			-	46	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current			-	138	Α
V_{SD}	Drain to Source Diode Forward Voltage V _{GS} = 0 V, I _{SD} = 46 A		-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 46 A,	-	800	-	ns
Q _{rr}	Reverse Recovery Charge $dI_F/dt = 100 \text{ A/}\mu\text{s}$		-	32	-	μС

Notes:

- ${\it 1. Repetitive\ rating: pulse\ width\ limited\ by\ maximum\ junction\ temperature.}$
- 2. I_{AS} = 9.2 A, V_{DD} = 50 V, R_{G} = 25 Ω , Starting T_{J} = 25°C
- 3. $I_{SD} \le$ 46 A, di/dt \le 200 A/ μ s, $V_{DD} \le$ BV $_{DSS}$, Starting T $_{J}$ = 25°C
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

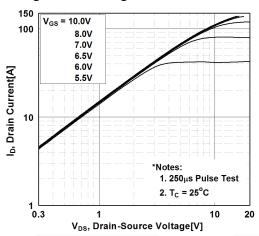


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

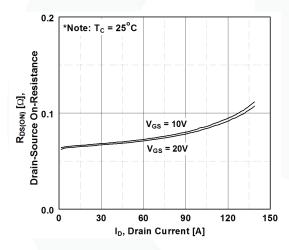


Figure 5. Capacitance Characteristics

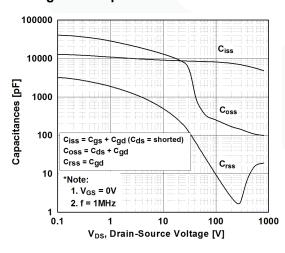


Figure 2. Transfer Characteristics

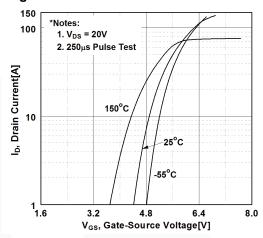


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

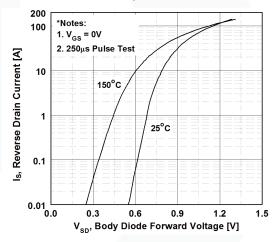
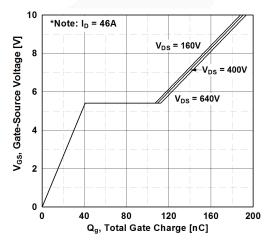


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

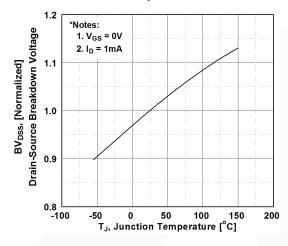


Figure 9. Maximum Safe Operating Area

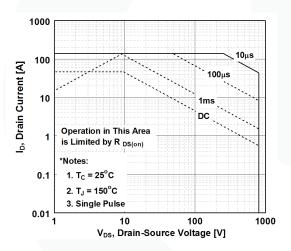


Figure 11. Eoss vs. Drain to Source Voltage

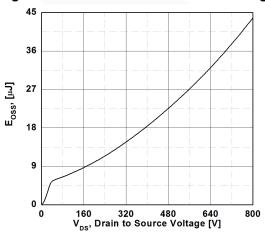


Figure 8. On-Resistance Variation vs. Temperature

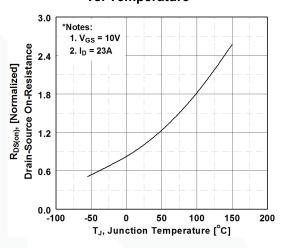
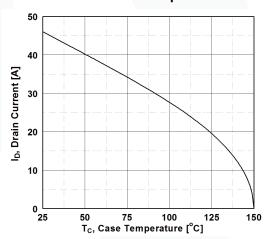


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve

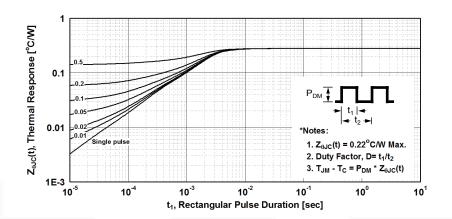


Figure 13. Gate Charge Test Circuit & Waveform

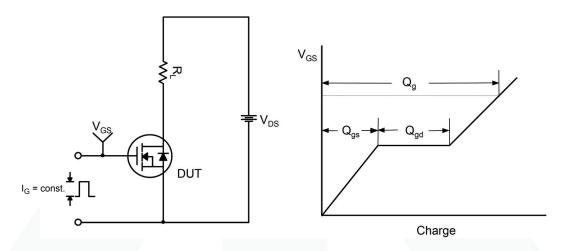


Figure 14. Resistive Switching Test Circuit & Waveforms

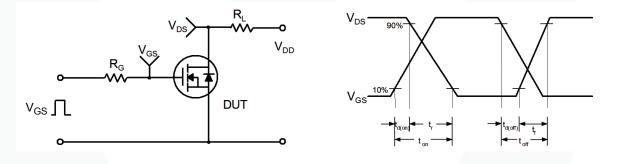
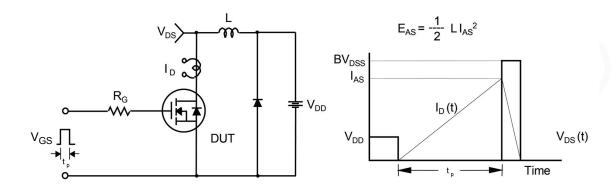


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms



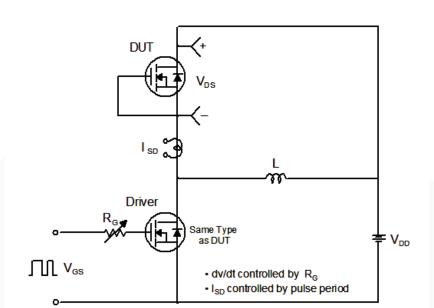
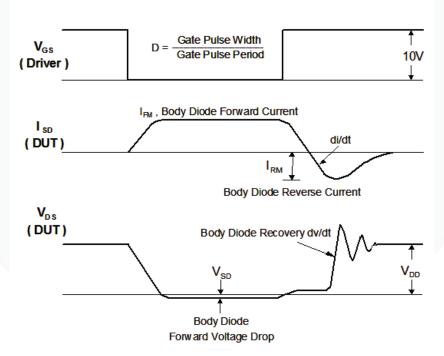


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Physical Dimensions

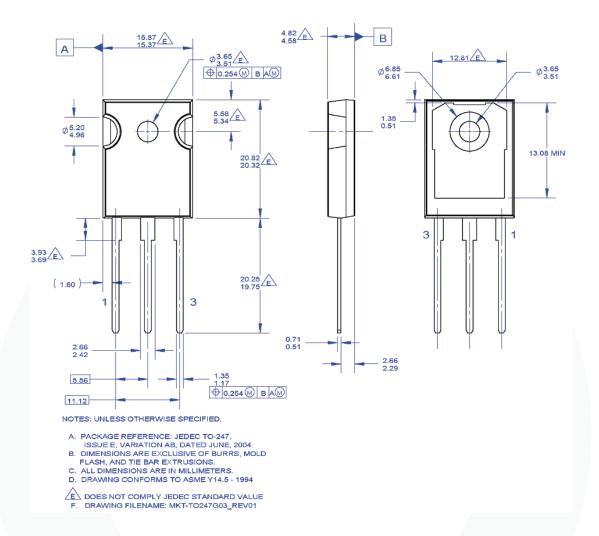


Figure 17. TO-247,MOLDED,3 LEAD,JEDEC AB LONG LEADS (Active)

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